

20V N-CHANNEL ENHANCEMENT MODE MOSFET

Low Package Profile, 0.42mm Maximum Package Height

Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2) Halogen and Antimony Free. "Green" Device (Note 3)

Very Low Gate Threshold Voltage, 1.0V Maximum

Product Summary

BV _{DSS}	R _{DS(ON)} Max	I _D Max T _A = +25°C
20V	0.99Ω @ V _{GS} = 4.5V	0.55A
	1.2Ω @ V _{GS} = 2.5V	0.50A
	1.8Ω @ V _{GS} = 1.8V	0.41A
	2.4Ω @ V _{GS} = 1.5V	0.35A

Description

This MOSFET is designed to minimize the on-state resistance $(R_{DS(ON)})$ yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

Applications

- General Purpose Interfacing Switch
- Power Management Functions
- Analog Switch

Mechanical Data

Features and Benefits

Low On-Resistance

ESD Protected Gate

0.62mm × 0.62mm Package Footprint

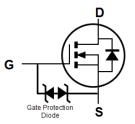
- Case: X2-DFN0606-3
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish—NiPdAu over Copper Leadframe. Solderable per MIL-STD-202, Method 208
- Weight: 0.001 grams (Approximate)



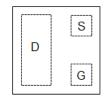


X2-DFN0606-3





Equivalent Circuit



Top View Package Pin Configuration

Ordering Information (Note 4)

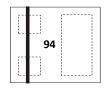
Part Number	Case	Packaging
DMN2991UFZ-7B	X2-DFN0606-3	10k/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information

X2-DFN0606-3



Top View

94 = Product Type Marking Code Bar Denotes Gate and Source Side



Maximum Ratings $(@T_A = +25^{\circ}C, \text{ unless otherwise specified.})$

Characteristic	Symbol	Value	Unit		
Drain-Source Voltage			V_{DSS}	20	V
Gate-Source Voltage			V_{GSS}	±8	V
Continuous Drain Current (Note 5) $V_{GS} = 4.5V$ Steady $T_A = +25^{\circ}C$ $T_A = +75^{\circ}C$			I _D	0.55 0.44	А
Maximum Body Diode Forward Current (Note 6)			I _S	0.7	Α
Pulsed Drain Current (380µs Pulse, Duty Cycle = 1%)			I _{DM}	1.5	Α

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Power Dissipation (Note 5)	Steady State	P_{D}	0.45	mW
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	R _{0JA}	279	°C/W
Power Dissipation (Note 6)	Steady State	P _D	0.53	mW
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	$R_{\theta JA}$	148	°C/W
Operating and Storage Temperature Range	·	T _J , T _{STG}	-55 to +150	°C

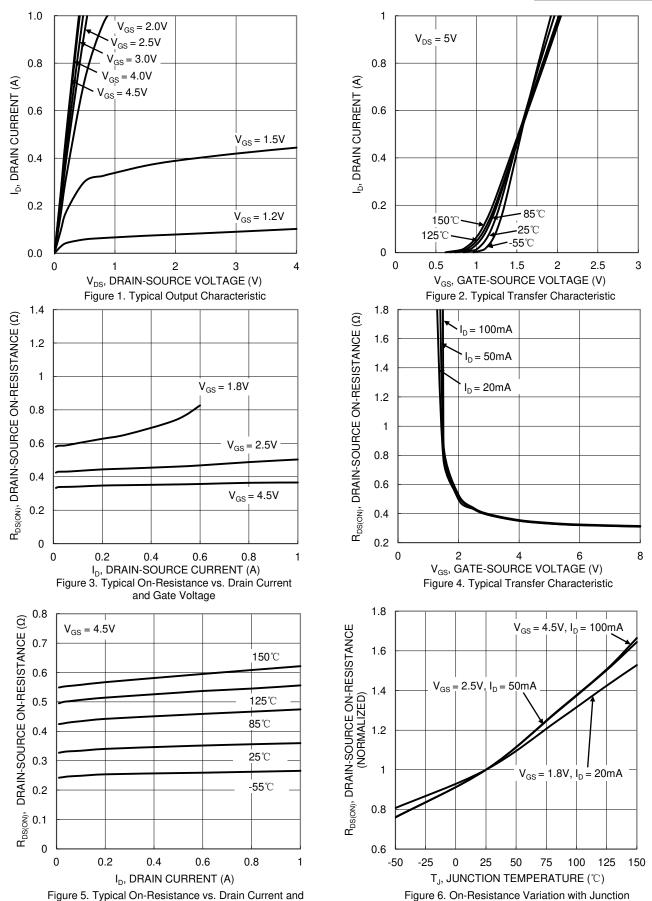
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)							
Drain-Source Breakdown Voltage	BV _{DSS}	20	_	_	V	$V_{GS} = 0V, I_D = 250\mu A$	
Zero Gate Voltage Drain Current	I _{DSS}	_	_	1	μΑ	V _{DS} = 16V, V _{GS} = 0V	
Gate-Source Leakage	I _{GSS}	_	_	1	μΑ	$V_{GS} = \pm 5V$, $V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage	V _{GS(TH)}	0.4	0.8	1.0	V	$V_{DS} = V_{GS}$, $I_D = 250\mu A$	
		_	0.60	0.99		$V_{GS} = 4.5V, I_D = 100mA$	
		_	0.75	1.2		$V_{GS} = 2.5V, I_D = 50mA$	
Static Drain-Source On-Resistance	R _{DS(ON)}	_	0.90	1.8	Ω	V _{GS} = 1.8V, I _D = 20mA	
		_	1.2	2.4		V _{GS} = 1.5V, I _D = 10mA	
		_	2.0	_		V _{GS} = 1.2V, I _D = 1mA	
Diode Forward Voltage	V_{SD}	_	0.6	1.0	V	V _{GS} = 0V, I _S = 150mA	
DYNAMIC CHARACTERISTICS (Note 8)							
Input Capacitance	C _{iss}	_	21.5	_	pF		
Output Capacitance	Coss	_	4.9	_	pF	$V_{DS} = 16V, V_{GS} = 0V,$ f = 1.0MHz	
Reverse Transfer Capacitance	C _{rss}	_	3.7	_	pF	-1 = 1.0IVII 12	
Total Gate Charge	Qg	_	0.35	_	nC		
Gate-Source Charge	Q _{gs}	_	0.07	_	nC	$V_{GS} = 4.5V, V_{DS} = 10V,$	
Gate-Drain Charge	Q _{gd}	_	0.08	_	nC	$I_D = 250 \text{mA}$	
Turn-On Delay Time	t _{D(ON)}	_	5.6	_	ns	$V_{DD} = 10V, V_{GS} = 4.5V,$ $R_{L} = 47\Omega, R_{g} = 10\Omega,$ $I_{D} = 200 \text{mA}$	
Turn-On Rise Time	t _R	_	4.9	_	ns		
Turn-Off Delay Time	t _{D(OFF)}	_	60.6	_	ns		
Turn-Off Fall Time	t _F	_	27.6	_	ns		
Reverse Recovery Time	t _{RR}	_	12.3	_	ns	$I_F = 1.0A$, di/dt = 100A/ μ s	
Reverse Recovery Charge	Q _{RR}	_	1.1	_	nC	I _F = 1.0A, di/dt = 100A/μs	

Notes:

- Device mounted on FR-4 PCB, with minimum recommended pad layout.
 Device mounted on FR-4 substrate PC board, 2oz copper, with thermal vias to bottom layer 1inch square copper plate.
 Short duration pulse test used to minimize self-heating effect.
 Guaranteed by design. Not subject to product testing.





Junction Temperature

Temperature



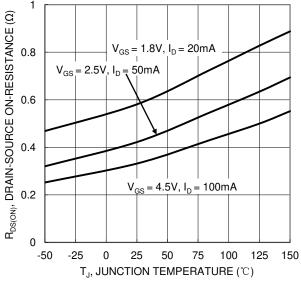


Figure 7. On-Resistance Variation with Junction Temperature

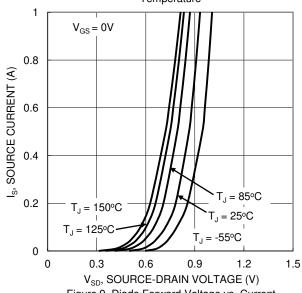


Figure 9. Diode Forward Voltage vs. Current

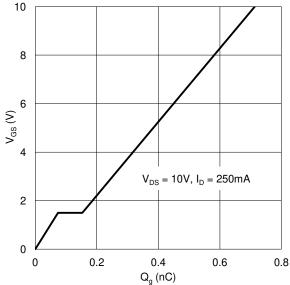


Figure 11. Gate Charge

1 $V_{GS(TH)},$ GATE THRESHOLD VOLTAGE (V) 0.9 $I_D = 1mA$ 8.0 $I_{D} = 250 \mu A$ 0.7 0.6 0.5 -50 -25 0 25 50 75 100 125 150

Figure 8. Gate Threshold Variation vs. Junction Temperature

T., JUNCTION TEMPERATURE (°C)

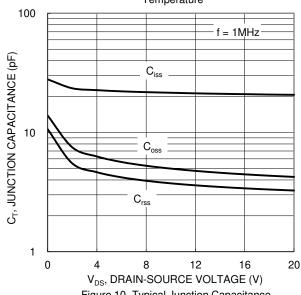
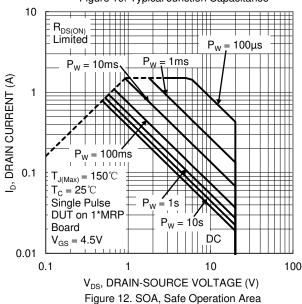


Figure 10. Typical Junction Capacitance





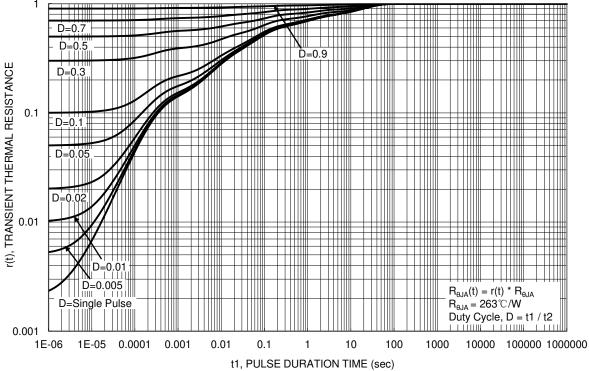
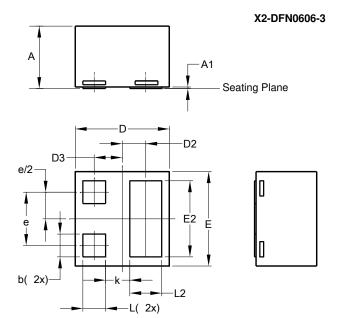


Figure 13. Transient Thermal Resistance



Package Outline Dimensions

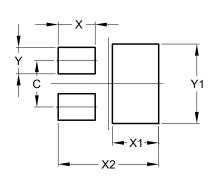
Please see http://www.diodes.com/package-outlines.html for the latest version.



X2-DFN0606-3				
Dim	Min	Тур		
Α	0.36	0.42	0.39	
A 1	0	0.05	0.02	
b	0.10	0.20	0.15	
D	0.57	0.67	0.62	
D2	0.155 BSC			
D3	0.185 BSC			
Е	0.57	0.67	0.62	
E2	0.40	0.60	0.50	
е	0.35 BSC			
k	0.16 REF			
L	0.09	0.21	0.15	
L2	0.11	0.31	0.21	
All Dimensions in mm				

Suggested Pad Layout

 $Please \ see \ http://www.diodes.com/package-outlines.html \ for \ the \ latest \ version.$



X2-DFN0606-3

Dimensions	Value (in mm)
С	0.350
Х	0.280
X1	0.350
X2	0.760
Υ	0.200
Y1	0.600



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